

AFGB30T65SQDN

IGBT for Automotive Applications

650 V, 30 A, D²PAK

Features

- Maximum Junction Temperature: $T_J = 175^\circ\text{C}$
- High Speed Switching Series
- $V_{CE(sat)} = 1.6\text{ V (typ.) @ } I_C = 30\text{ A}$
- Low VF Soft Recovery Co-packaged Diode
- AEC-Q101 Qualified
- 100% of the Parts are Dynamically Tested (Note 1)

Typical Applications

- Automotive On Board Charger
- Automotive DC/DC Converter for HEV

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Symbol | Value | Unit |
|---|----------------|-------------|------------------|
| Collector-to-Emitter Voltage | V_{CES} | 650 | V |
| Gate-to-Emitter Voltage | V_{GES} | ± 20 | V |
| Transient Gate-to-Emitter Voltage | V_{GES} | ± 30 | V |
| Collector Current ($T_C = 25^\circ\text{C}$) | I_C | 60 | A |
| Collector Current ($T_C = 100^\circ\text{C}$) | | 30 | A |
| Pulsed Collector Current (Note 2) | I_{CM} | 120 | A |
| Diode Forward Current ($T_C = 25^\circ\text{C}$) | I_F | 40 | A |
| Diode Forward Current ($T_C = 100^\circ\text{C}$) | | 20 | A |
| Pulsed Diode Maximum Forward Current (Note 2) | I_{FM} | 120 | A |
| Maximum Power Dissipation ($T_C = 25^\circ\text{C}$) | P_D | 220 | W |
| Maximum Power Dissipation ($T_C = 100^\circ\text{C}$) | | 110 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to +175 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

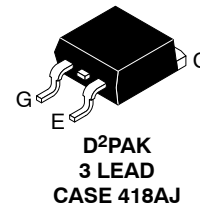
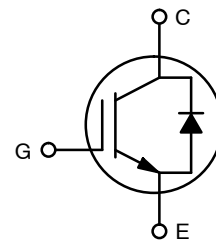
1. $V_{CC} = 400\text{ V}, V_{GE} = 15\text{ V}, I_C = 90\text{ A}, R_G = 100\ \Omega$, Inductive Load
2. Repetitive rating: pulse width limited by max. Junction temperature
3. Surface-mounted on FR4 board using 1 in^2 pad size, 1 oz Cu pad.
4. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.



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| BV_{CES} | $V_{CE(sat)}$ TYP | I_C MAX |
|------------|-------------------|-----------|
| 650 V | 1.6 V | 120 A |



MARKING DIAGRAM



- &Y = ON Semiconductor Logo
- &Z = Assembly Plant Code
- &3 = 3-Digit Date Code
- &K = 2-Digit Lot Traceability Code
- AFGB30T65SQDN = Specific Device Code

ORDERING INFORMATION

| Device | Package | Shipping† |
|---------------|----------------|-------------------------|
| AFGB30T65SQDN | D2PAK (TO-263) | 800 Units / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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Table 1. THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Max | Unit |
|--|-----------------|------|------|
| Thermal Resistance Junction-to-Case, for IGBT | $R_{\theta JC}$ | 0.68 | °C/W |
| Thermal Resistance Junction-to-Case, for Diode | $R_{\theta JC}$ | 1.55 | |
| Thermal Resistance Junction-to-Ambient | $R_{\theta JA}$ | 40 | |

Table 2. ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|--|-------------------------------|--|-------|-------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Collector-to-Emitter Breakdown Voltage | BV_{CES} | $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$ | 650 | – | – | V |
| Temperature Coefficient of Breakdown Voltage | $\Delta V_{CES} / \Delta T_J$ | $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$ | – | 0.6 | – | V/°C |
| Collector Cut-Off Current | I_{CES} | $V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$ | – | – | 250 | μA |
| G-E Leakage Current | I_{GES} | $V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$ | – | – | ±400 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | $V_{GE(th)}$ | $V_{GE} = V_{CE}, I_C = 30\text{ mA}$ | 3.0 | 4.5 | 6.0 | V |
| Collector-to-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 30\text{ A}, V_{GE} = 15\text{ V}, T_C = 25^\circ\text{C}$ | – | 1.6 | 2.1 | V |
| | | $I_C = 30\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$ | – | 1.92 | – | V |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{ies} | $V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | – | 1871 | – | pF |
| Output Capacitance | C_{oes} | | – | 44 | – | |
| Reverse Transfer Capacitance | C_{res} | | – | 7 | – | |
| SWITCHING CHARACTERISTICS | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CC} = 400\text{ V}, I_C = 30\text{ A}, R_G = 6\ \Omega,$ $V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$ | – | 14.5 | – | ns |
| Rise Time | t_r | | – | 16 | – | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | – | 63.2 | – | ns |
| Fall Time | t_f | | – | 8.3 | – | ns |
| Turn-On Switching Loss | E_{on} | | – | 0.783 | – | mJ |
| Turn-Off Switching Loss | E_{off} | | – | 0.160 | – | mJ |
| Total Switching Loss | E_{ts} | – | 0.943 | – | mJ | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CC} = 400\text{ V}, I_C = 30\text{ A}, R_G = 6\ \Omega,$ $V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 175^\circ\text{C}$ | – | 12.8 | – | ns |
| Rise Time | t_r | | – | 20.8 | – | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | – | 67.2 | – | ns |
| Fall Time | t_f | | – | 11.5 | – | ns |
| Turn-On Switching Loss | E_{on} | | – | 1.01 | – | mJ |
| Turn-Off Switching Loss | E_{off} | | – | 0.369 | – | mJ |
| Total Switching Loss | E_{ts} | – | 1.379 | – | mJ | |
| Total Gate Charge | Q_g | $V_{CE} = 400\text{ V}, I_C = 30\text{ A},$ $V_{GE} = 15\text{ V}$ | – | 56 | – | nC |
| Gate-to-Emitter Charge | Q_{ge} | | – | 11 | – | nC |
| Gate-to-Collector Charge | Q_{gc} | | – | 14 | – | nC |

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Table 2. ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-------------------------------|-----------|---|-----|-----|-----|---------------|
| DIODE CHARACTERISTICS | | | | | | |
| Diode Forward Voltage | V_{FM} | $I_F = 20\text{ A}$ | – | 1.5 | 2.1 | V |
| Reverse Recovery Energy | E_{rec} | $I_F = 20\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$, $T_C = 25^\circ\text{C}$ | – | 22 | – | μJ |
| Diode Reverse Recovery Time | t_{rr} | | – | 131 | – | ns |
| Diode Reverse Recovery Charge | Q_{rr} | | – | 348 | – | nC |
| Reverse Recovery Energy | E_{rec} | $I_F = 20\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$, $T_C = 175^\circ\text{C}$ | – | 100 | – | μJ |
| Diode Reverse Recovery Time | t_{rr} | | – | 245 | – | ns |
| Diode Reverse Recovery Charge | Q_{rr} | | – | 961 | – | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

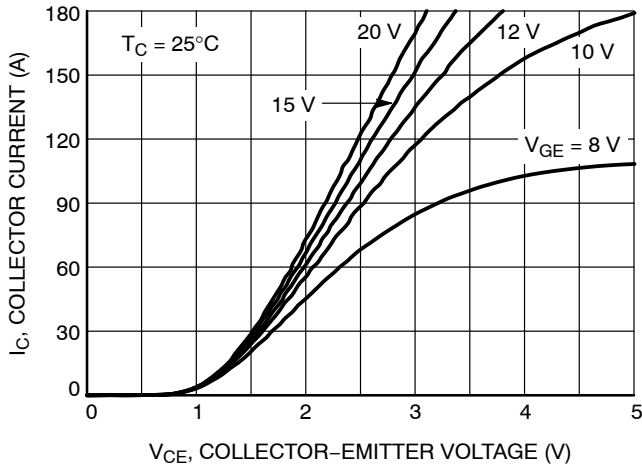


Figure 1. Typical Output Characteristics (25°C)

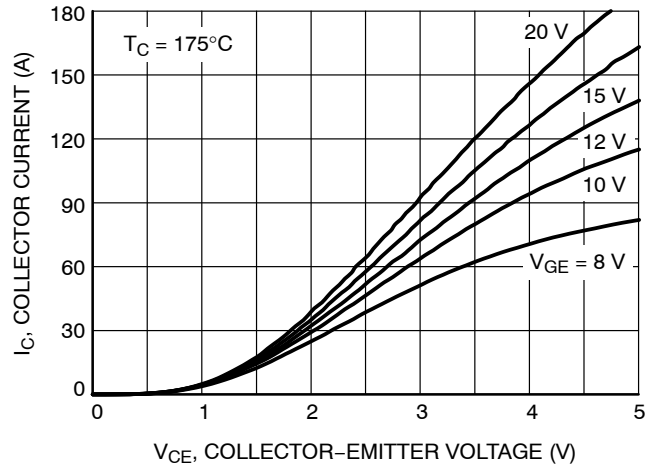


Figure 2. Typical Output Characteristics (175°C)

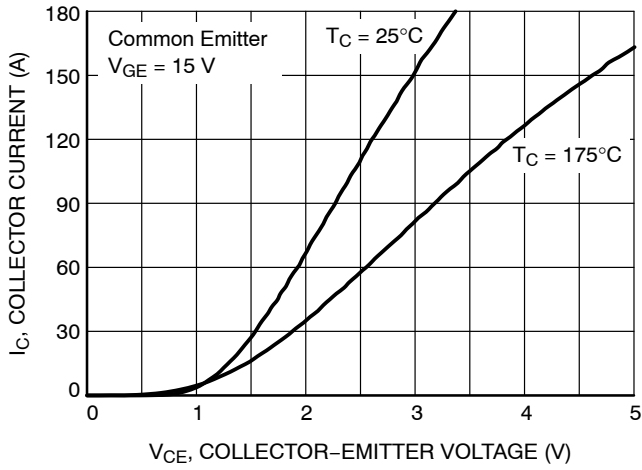


Figure 3. Typical Saturation Voltage Characteristics

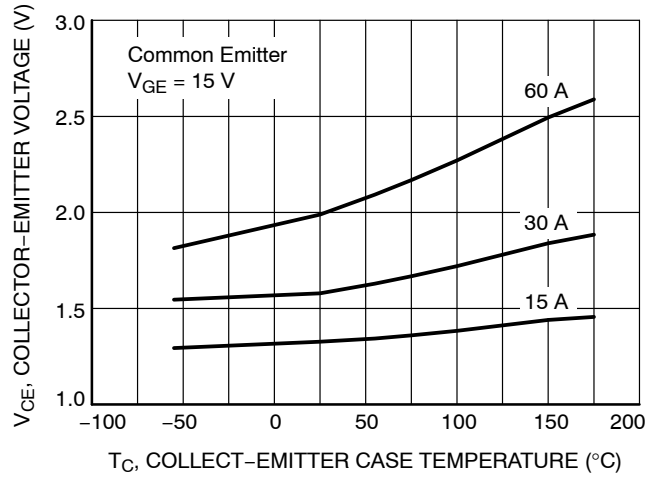


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

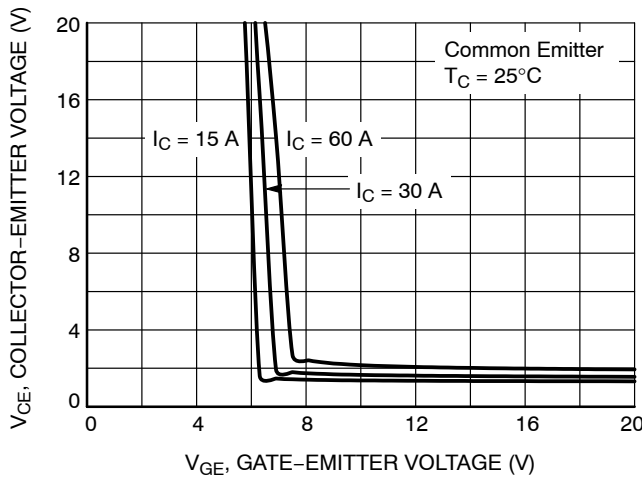


Figure 5. Saturation Voltage vs. V_{GE} (25°C)

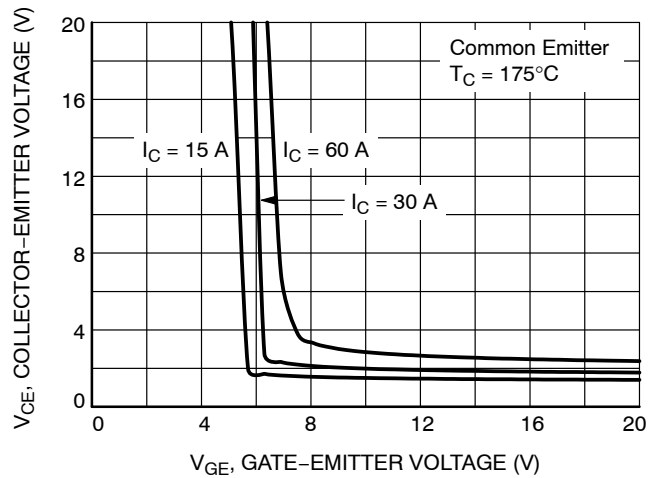


Figure 6. Saturation Voltage vs. V_{GE} (175°C)

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TYPICAL CHARACTERISTICS

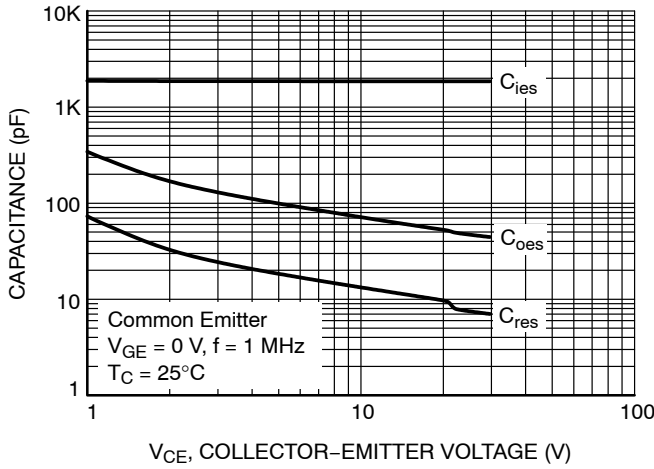


Figure 7. Capacitance Characteristics

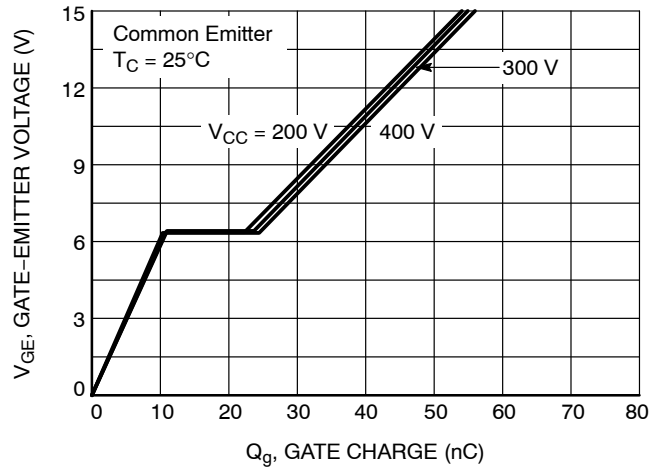


Figure 8. Gate Charge Characteristics

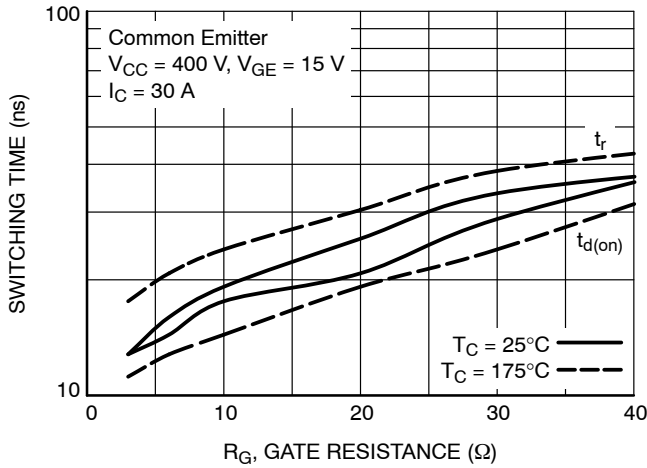


Figure 9. Turn-on Characteristics vs. Gate Resistance

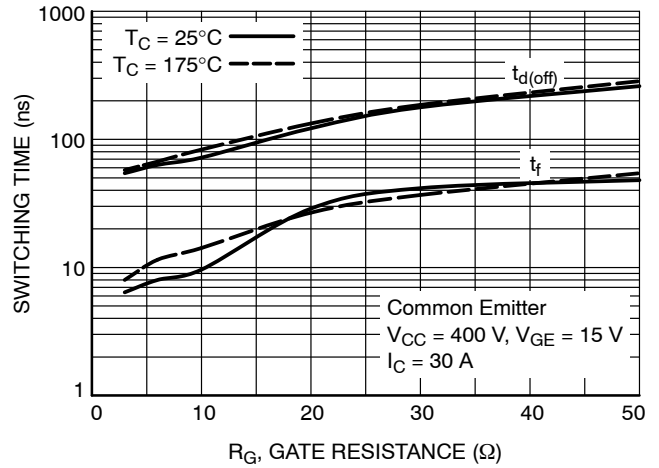


Figure 10. Turn-off Characteristics vs. Gate Resistance

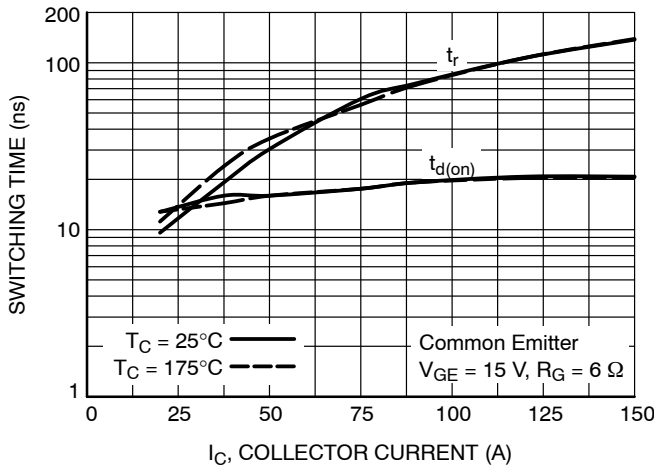


Figure 11. Turn-on Characteristics vs. Collector Current

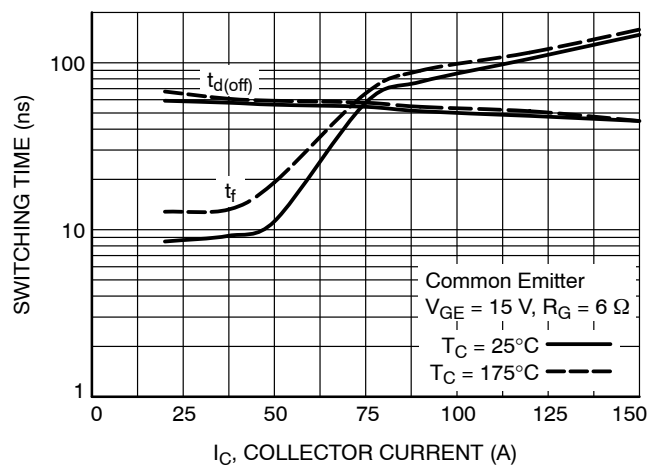


Figure 12. Turn-off Characteristics vs. Collector Current

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TYPICAL CHARACTERISTICS

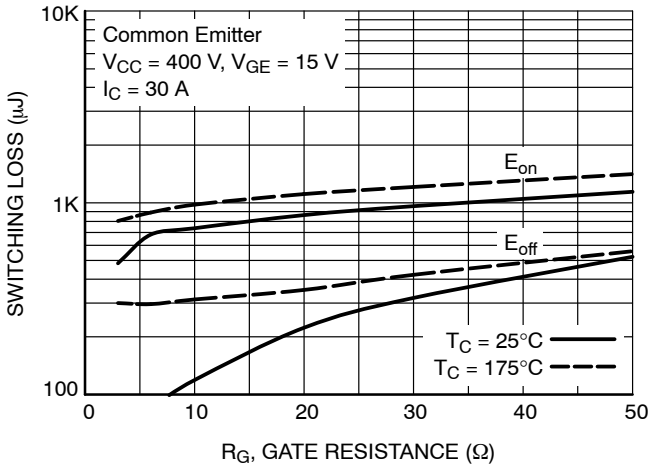


Figure 13. Switching Loss vs. Gate Resistance

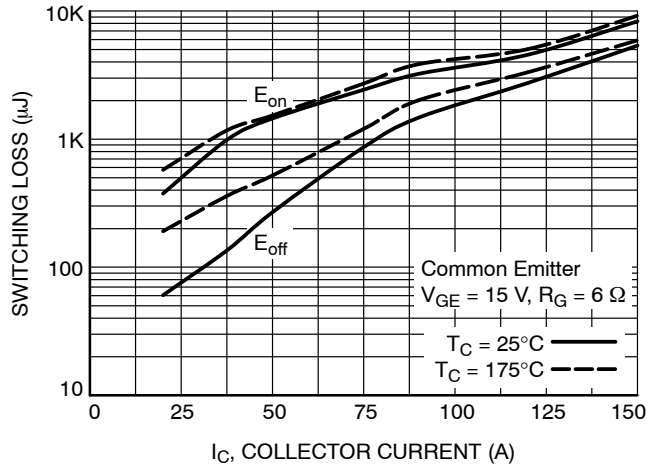


Figure 14. Switching Loss vs. Collector Current

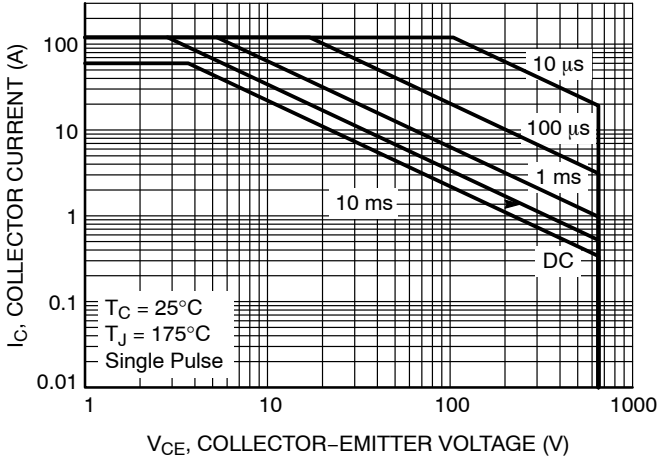


Figure 15. SOA Characteristics

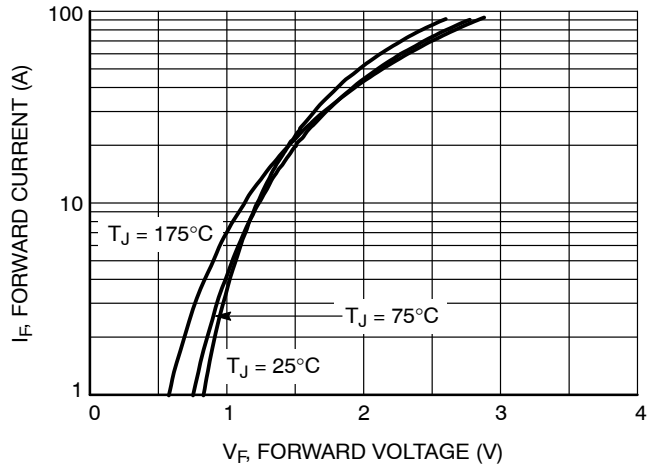


Figure 16. Forward Characteristics

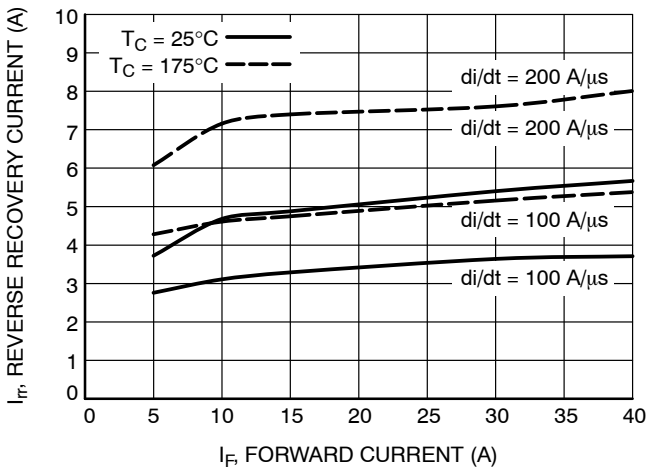


Figure 17. Reverse Recovery Current

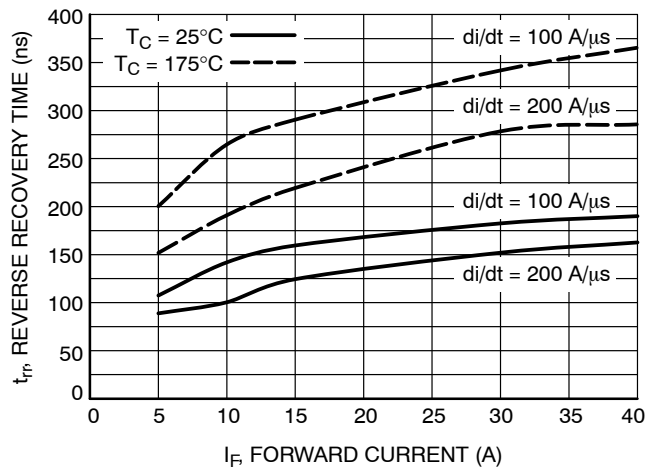


Figure 18. Reverse Recovery Time

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TYPICAL CHARACTERISTICS

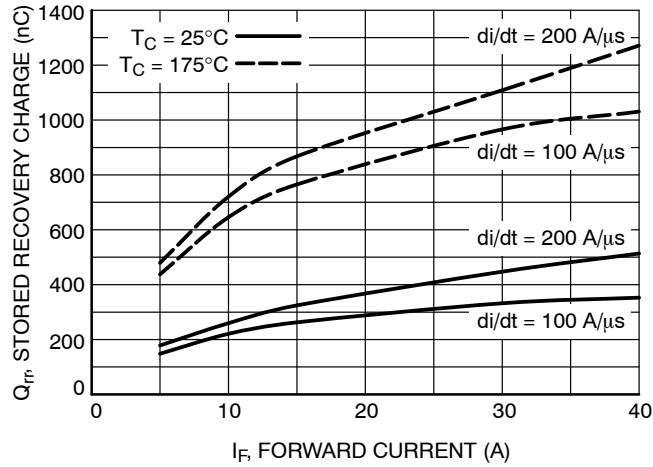


Figure 19. Stored Charge

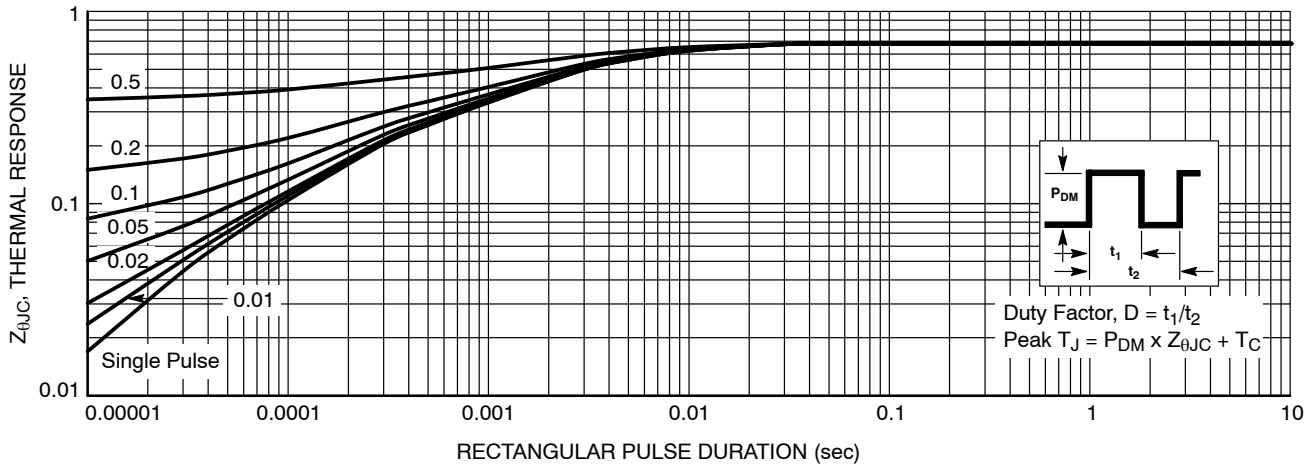


Figure 20. Transient Thermal Impedance of IGBT

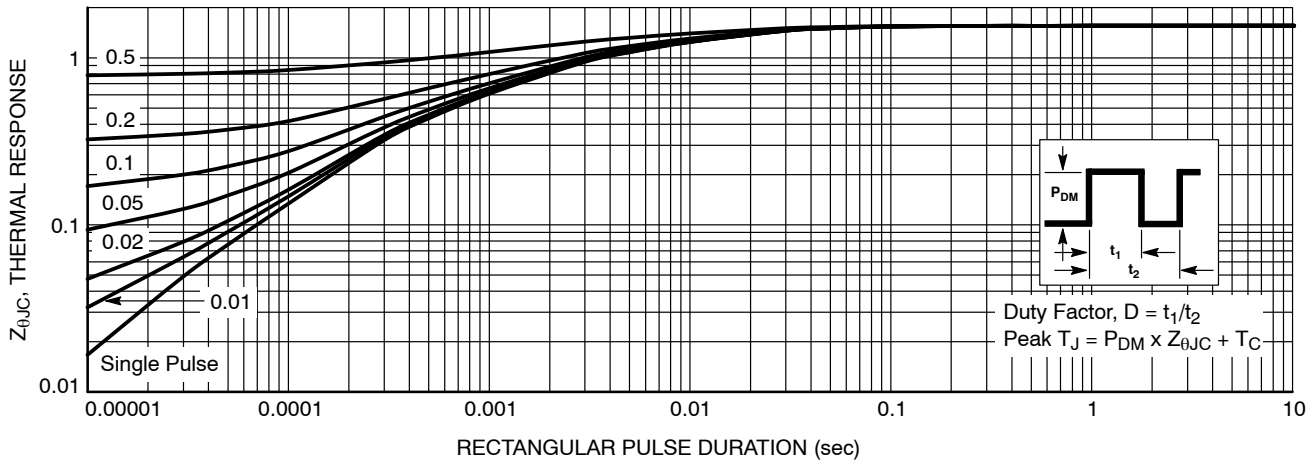
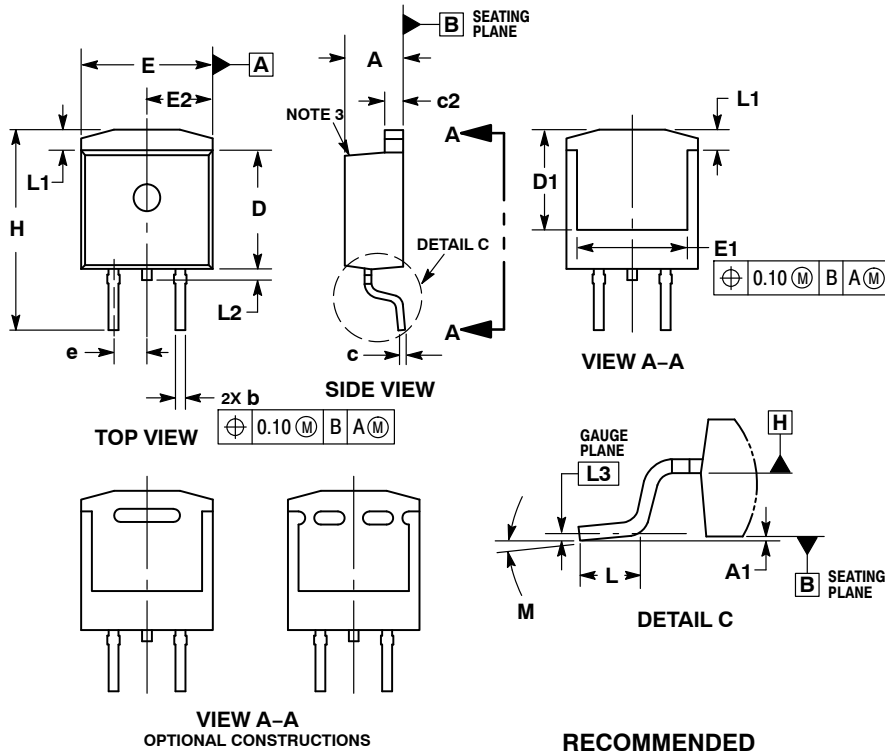


Figure 21. Transient Thermal Impedance of Diode

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PACKAGE DIMENSIONS

D²PAK-3 (TO-263, 3-LEAD)
CASE 418AJ
ISSUE C

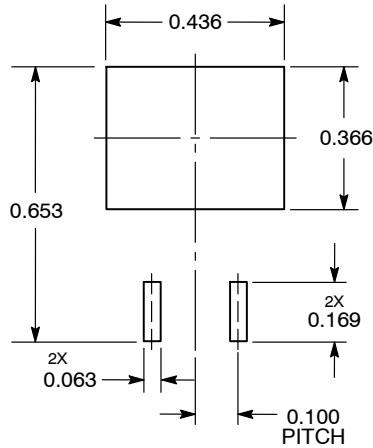


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CHAMFER OPTIONAL
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1 AND E1.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.160 | 0.190 | 4.06 | 4.83 |
| A1 | 0.000 | 0.010 | 0.00 | 0.25 |
| b | 0.020 | 0.039 | 0.51 | 0.99 |
| c | 0.012 | 0.029 | 0.30 | 0.74 |
| c2 | 0.045 | 0.065 | 1.14 | 1.65 |
| D | 0.330 | 0.380 | 8.38 | 9.65 |
| D1 | 0.260 | ---- | 6.60 | ---- |
| E | 0.380 | 0.420 | 9.65 | 10.67 |
| E1 | 0.245 | ---- | 6.22 | ---- |
| e | 0.100 BSC | ---- | 2.54 BSC | ---- |
| H | 0.575 | 0.625 | 14.60 | 15.88 |
| L | 0.070 | 0.110 | 1.78 | 2.79 |
| L1 | ---- | 0.066 | ---- | 1.68 |
| L2 | ---- | 0.070 | ---- | 1.78 |
| L3 | 0.010 BSC | ---- | 0.25 BSC | ---- |
| M | -8° | 8° | -8° | 8° |

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: INCHES

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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Электронная почта: org@eplast1.ru

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